

# DMC26404

Silicon NPN epitaxial planar type

For digital circuits

## ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

## ■ Marking Symbol: J4

## ■ Basic Part Number

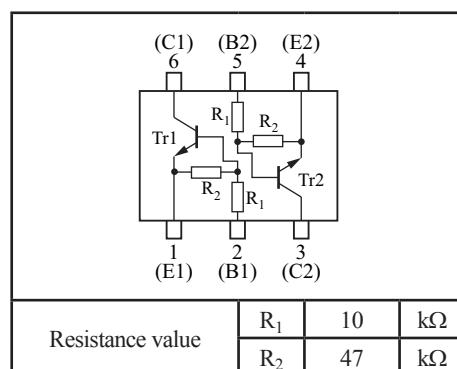
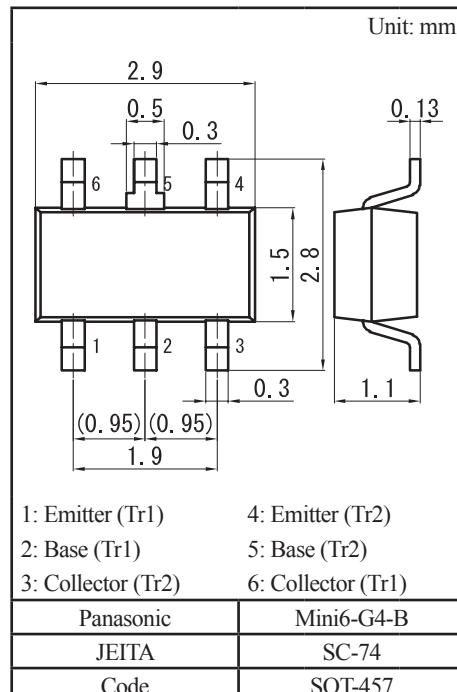
Dual DRC2114Y (Individual)

## ■ Packaging

DMC26404R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

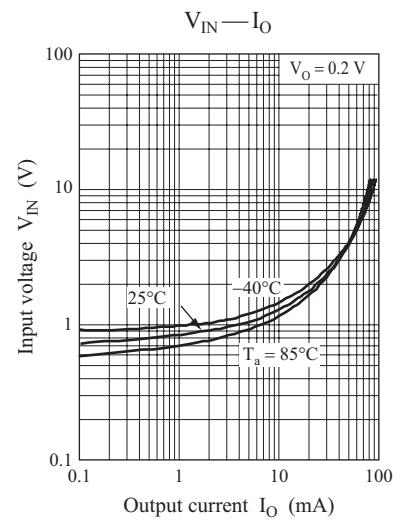
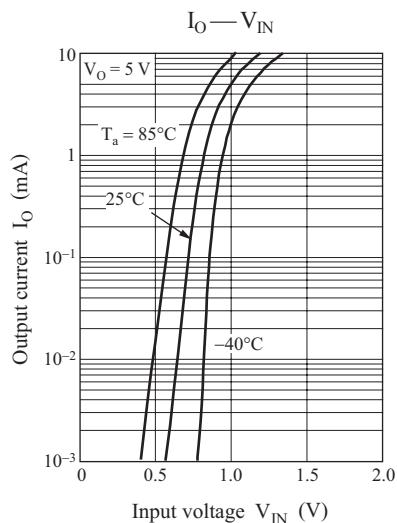
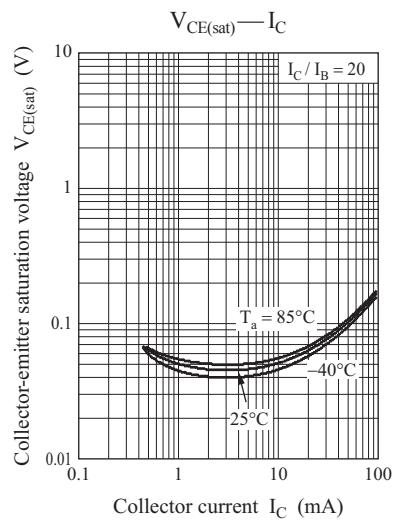
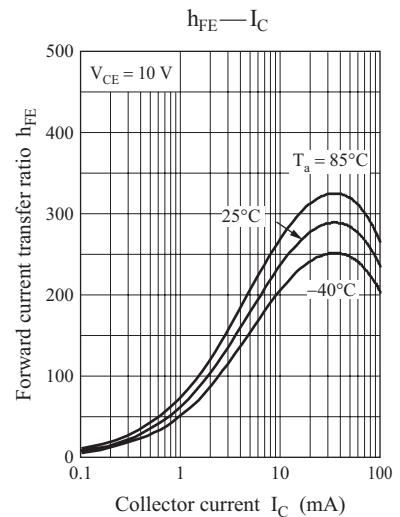
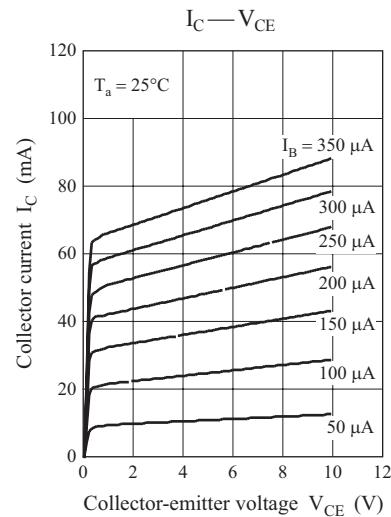
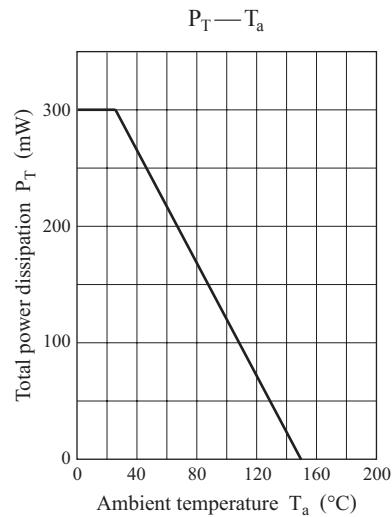
	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Tr2	Collector current	$I_C$	100	mA
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	°C
	Operating ambient temperature	$T_{opr}$	-40 to +85	°C
	Storage temperature	$T_{stg}$	-55 to +150	°C



## ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

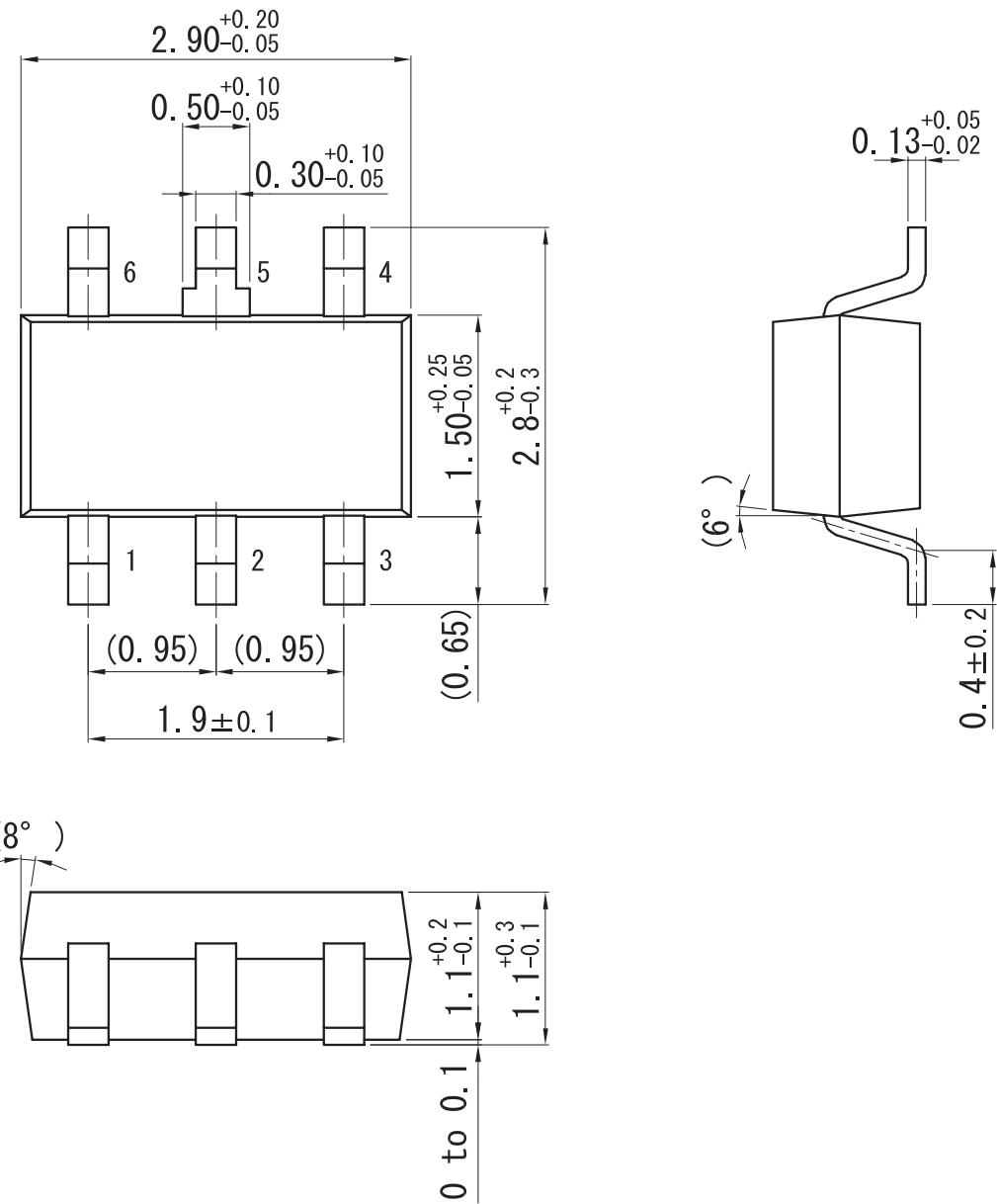
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			0.2	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	$V_{I(on)}$	$V_{CE} = 0.2 \text{ V}, I_C = 5 \text{ mA}$	1.7			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = 5 \text{ V}, I_C = 100 \mu\text{A}$			0.5	V
Input resistance	$R_1$		-30%	10	+30%	kΩ
Resistance ratio	$R_1 / R_2$		0.17	0.21	0.25	—

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

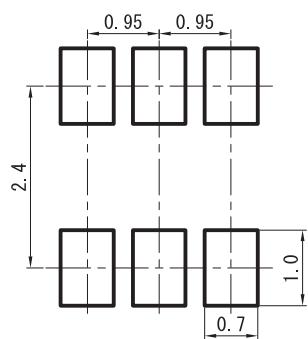


## Mini6-G4-B

Unit: mm



## ■ Land Pattern (Reference) (Unit: mm)



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